

**Inchange Semiconductor**

**Product Specification**

**Silicon NPN Power Transistors**

**BUT56AF**

**DESCRIPTION**

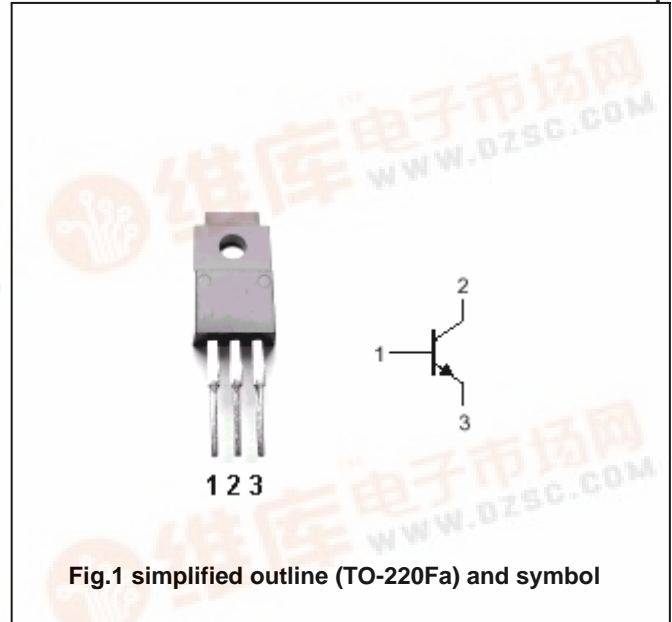
- With TO-220Fa package
- High voltage;high speed
- High power dissipation

**APPLICATIONS**

- Switching mode power supply

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolut maximum ratings (Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1000	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	450	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-peak		10	A
I <sub>BM</sub>	Base current-peak		4	A
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25	50	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-65~150	

## Silicon NPN Power Transistors

## BUT56AF

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =100mA ; L <sub>C</sub> =125mH	450			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.8A			2.0	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1000V ; V <sub>BE</sub> =0 T <sub>j</sub> =150			1.0 2.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	15		45	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =2V	4			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V ; f=1.0MHz		10		MHz

## Switching times

t <sub>off</sub>	Turn-off time	I <sub>C</sub> =4A ; I <sub>B1</sub> =-I <sub>B2</sub> =1.25A t <sub>p</sub> =20 μs			4	μs
t <sub>f</sub>	Fall time				1	μs

